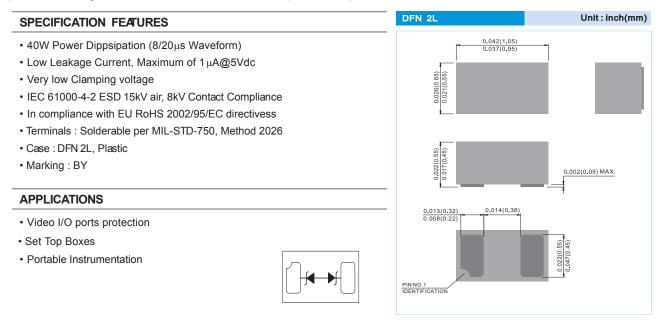


PJSD05LCFN2

BI-DIRECTIONAL ESD PROTECTION DIODE

This bi-directional TVS has been designed to protect sensitive equipment against ESD and to prevent Latch-Up events in CMOS circuitry operating at 5Vdc and below. This offers an integrated solution to protect a single data line where the board space is a premium.



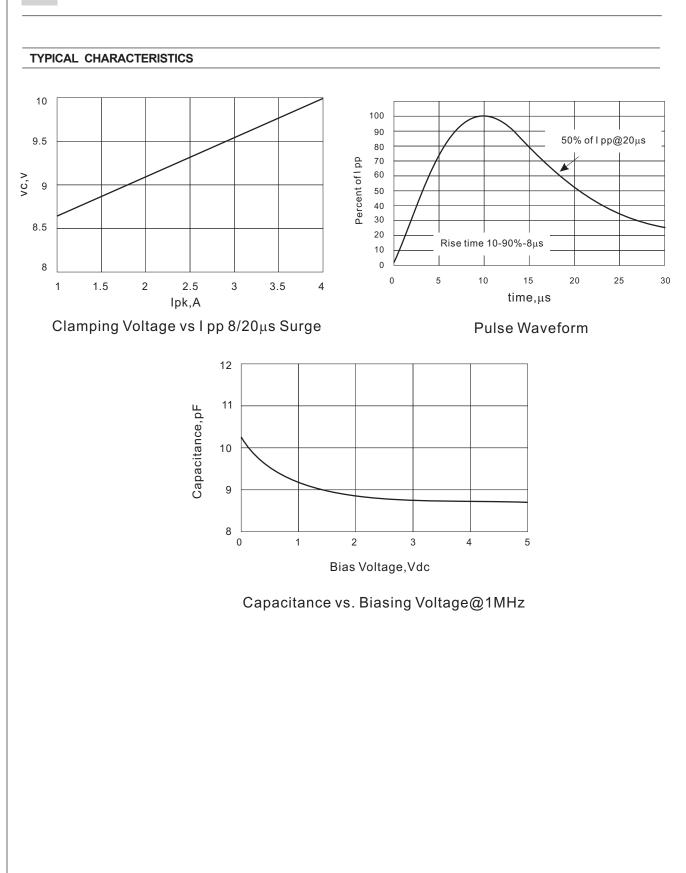
MAXIMUM RATINGS

Rating	Symbol	Value	Units
Peak Pulse Power (8/20 μs Waveform)	Ррр	40	W
Peak Pulse Current (8/20 μs Waveform)	I ррм	4	A
ESD Voltage (HBM)	Vesd	>25	kV
Operating Junction and Storage Temperature Range	Тј,Тѕтс	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	Vwrm		-	-	5.0	V
Reverse Breakdown Voltage	Vbr	IBR=1mA	5.78	-	7.82	V
Reverse Leakage Current	IR	V _R =5V	-	-	1.0	μΑ
Clamping Voltage (8/20µs)	Vc	IPP=4A	-	-	10	V
Off State Junction Capacitance	CJ	0 Vdc Bias f=1MHz	-	-	15	pF

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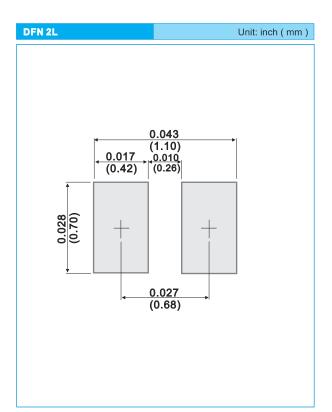
PJSD05LCFN2





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MOUNTING PAD LAYOUT



ORDER INFORMATION

Packing information

T/R - 8K per 7" plastic Reel

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